

July 19, 2011

## Product Specifications of the New Power MOSFET Devices

Part number	Package	Drain-to-source voltage [VDSS] (V)	Gate-to-source voltage [VGSS] (V)	Drain current [ID] (A)	On-state resistance [RDS(on)] (VGSS = 10 V) (mΩ)		Total gate charge [Qg] (nC)	Input capacitance [Ciss] (pF)
					Typ	Max		
N0412N	TO-220	40	±20	100	3.0	3.7	97	6000
N0434N	TO-262	40	±20	100	3.0	3.7	97	6000
N0413N	TO-263	40	±20	100	2.7	3.3	97	6000
N0602N	TO-220	60	±20	100	3.6	4.6	148	8000
N0603N	TO-262	60	±20	100	3.6	4.6	148	8000
N0601N	TO-263	60	±20	100	3.3	4.2	148	8000